Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	("20040245980").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/26 08:12
S2	1	"l3" and (surface adj potential) near5 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 10:11
S3	2	("5945832").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/26 09:06
S4	3	("3995216" | "5457396").PN. OR ("5945832").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/26 08:51
S5	5209	(surface adj potential) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 07:17
S6	4	"l9" and ((scanninng adj surface adj potential adj microscopy) SSPM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 07:28
S7	2	("4539640").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/26 09:32

S8	7	(molecul$5 adj electric$5 adj conduct$5) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 12:12
S9	5	S8 and @ad<"20040402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 10:15
S10	2	((surface adj potential) adj3 (substrate material $5film coat$3 layer sheet pad wafer film lamina level plane paper web medium media material)) near5 ((surface adj potential) adj ((self adj assembl$5 adj mono$1layer) SAM)) near5 (change variation difference modification adjustment alternation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:24
S11	320	((self adj assembl$5 adj mono$1layer) SAM) near3 compound	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 09:56
S12	177	(((self adj assembl$5 adj mono$1layer) SAM) near3 compound) same (substrate material $5film coat$3 layer sheet pad wafer film lamina level plane paper web medium media material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 09:56
S13	113	(((self adj assembl$5 adj mono$1layer) SAM) near3 compound) with (substrate material $5film coat$3 layer sheet pad wafer film lamina level plane paper web medium media material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 09:58
S14	330	(324/691.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 07:22

S15	237	(324/649,600.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:37
S16	1	S15 and (surface adj potential) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:05
S17	4946	S5 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 10:12
S18	44	S17 and ((self adj assembl$5 adj mono$1layer) SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 12:28
S19	4	S17 and ((scanninng adj surface adj potential adj microscopy) SSPM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 14:56
S20	3	S8 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:26
S21	278	S11 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 10:21

S22	150	S12 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 10:22
S23	95	S13 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 14:58
S24	4	S21 and (surface adj potential)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 10:37
S25	1	S22 and (surface adj potential)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:00
S26	1	S23 and (surface adj potential)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 10:54
S27	1	S21 and (surface adj potential) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 14:59
S28	100	S21 and (change variation difference modification adjustment alternation) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 10:34

S29	62	S22 and (change variation difference modification adjustment alternation) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 10:35
S30	50	S23 and (change variation difference modification adjustment alternation) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 10:35
S31	2	S28 and (surface adj potential)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:01
S32	3	S11 and (surface adj potential) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:06
S33	1	S17 and ((self adj assembl$5 adj mono$1layer) SAM) with compound	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:12
S34	2	S17 and ((self adj assembl$5 adj mono$1layer) SAM) same compound	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:12
S35	3	(surface adj potential) near3 ((self adj assembl$5 adj mono$1layer) SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:25

S36	4483	((surface adj (voltage potential)) near3 (substrate material $5film coat$3 layer sheet pad wafer film lamina level plane paper web medium media material))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:26
S37	3	(surface adj (voltage potential)) near3 ((self adj assembl$5 adj mono$1layer) SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:27
S38	2	S36 and S37	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:26
S39	0	S38 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 12:13
S40	0	S37 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:27
S41	3	(surface adj (voltage potential)) with ((self adj assembl$5 adj mono$1layer) SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 11:28
S42	36	molecul$5 near3 electric$5 near3 conduct$5 near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 15:30

S43	27	S42 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 12:42
S44	0	S43 and ((scanninng adj surface adj potential adj (map$5 microscopy)) SSPM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 12:42
S45	3	S43 and ((self adj assembl$5 adj mono$1layer) SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 12:41
S46	33564	((self adj assembl$5 adj mono$1layer) SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 15:14
S47	29196	S46 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 14:32
S48	0	S47 and ((scanninng adj surface adj potential adj (map$5 microscopy)) SSPM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 14:25
S49	83	scan$5 with surface same potential same interfac$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 14:32

S50	75	S49 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 07:22
S51	56	S50 and $5layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 14:34
S52	83	(scan$5 with surface) same potential same interfac$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 07:29
S53	9	(scan$5 with map$5) same potential same interfac$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 14:36
S54	28	((scanninng adj surface adj potential adj microscopy) SSPM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 08:42
S55	25	S54 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 14:58
S56	4	S55 and (surface adj potential) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 15:00

S57	2	S55 and ((self adj assembl$5) SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 15:16
S58	8	S55 and ((self adj assembl$5) self $1assembl$5 SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 07:27
S59	2	S55 and ((self adj assembl$5) self$1assembl$5 SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 15:17
S60	1798	((surface adj potential) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)) with (substrate material $5film coat$3 layer sheet pad wafer film lamina level plane paper web medium media material $5conduct$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 07:22
S61	1694	S60 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 08:25
S62	547	S61 and (change variation difference modification adjustment alternation) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 08:44
S64	5	S62 and ((self adj assembl$5) self$1assembl$5 SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 08:23

S65	4	S64 and (scan$5 with surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 08:25
S66	213	compound near3 form$3 near3 ((self adj assembl$5) self$1assembl$5 SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 15:36
S67	159	S66 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 08:43
S68	67	S67 and compound near3 ((self adj assembl$5) self$1assembl$5 SAM) near5 (substrate material $5film coat$3 layer sheet pad wafer film lamina level plane paper web medium media material $5conduct$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 08:26
S69	28	(((scanninng near1 surface) adj potential adj microscopy) SSPM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:03
S70	25	S69 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 08:43
S71	4	S70 and ((change variation difference modification adjustment alternation) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)) same ((surface interfac$3) adj (voltage potential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:56

S72	963	(324/750-753.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 15:57
S73	588	molecul$3 near3 conduct$5 near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 07:20
S74	484	S73 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 15:34
S75	48	S74 and (plural$5 number multipl$5 series several set) near2 compound	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 07:24
S76	10	S75 and ((self adj assembl$5) self$1assembl$5 SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 07:28
S77	11750	molecul$3 same ((resist$5 conduct$5) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:52
S78	10154	S77 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 07:22

S79	1039	S78 and (((plural$5 number multipl$5 series several set) near2 compound) non$1homogeneous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:40
S80	114	S79 and ((self adj assembl$5) self$1assembl$5 SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 14:30
S81	19	S80 and ((change variation difference modification adjustment alternation) same (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)) same ((surface interfac$3) adj (voltage potential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:00
S82	215	compound near3 form$3 near3 ((self adj assembl$5) self$1assembl$5 SAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 07:51
S83	159	S82 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:51
S84	67	S83 and compound near3 ((self adj assembl$5) self$1assembl$5 SAM) near5 (substrate material $5film coat$3 layer sheet pad wafer film lamina level plane paper web medium media material $5conduct$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 07:56
S85	0	S84 and ((change variation difference modification adjustment alternation) same (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7)) same ((surface interfac$3) adj (voltage potential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:00

S86	0	S84 and (((scanninng near1 surface) adj potential adj microscopy) SSPM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:04
S87	0	S83 and (((scanninng near1 surface) adj potential adj microscopy) SSPM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:04
S88	3	S84 and molecul$3 same ((resist$5 conduct$5) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:08
S89	15	S84 and (((plural$5 number multipl$5 series several set) near2 compound) non$1homogeneous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:46
S90	90509	(plural$5 number multipl$5 series several set non$1homogeneous) near2 compound	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:14
S91	80285	S90 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:15
S92	543	S91 and molecul$3 same ((resist$5 conduct$5) near3 (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 determin$3 identif$7))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:53

S93	20	S92 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:29
S94	18	S93 and (anal$5 $3valuat$5 compar$5) near3 ((surface interfac$3) adj (voltage potential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:00
S95	0	S93 and compar$5 near3 ((surface interfac$3) adj (voltage potential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:00
S96	0	S92 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential)) near3 (field area portion section zone region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:07
S97	50409	(plural$5 number multipl$5 series several set non$1homogeneous) near2 molecule	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:14
S98	43646	S97 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:15
S99	6	S98 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 $6molecular near3 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:42

S100	202	S98 and $6molecular near3 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:27
S101	173	S100 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:28
S102	0	S101 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:50
S103	447	(324/692,693.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:38
S104	481	(324/719,722.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:51
S105	1188	(324/439,457,458.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 14:48
S106	1	S103 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near4 $6molecular near4 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:48

S107	0	S104 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near4 $6molecular near4 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:44
S108	1	S105 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near4 $6molecular near4 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:49
S109	388	(324/713.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:14
S110	0	S109 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near4 $6molecular near4 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:48
S111	85	(check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near4 $6molecular near4 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:51
S112	68	S111 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:52
S113	0	S112 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:44

S114	69	(check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near4 (molecular intra$1molecular) near4 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:16
S115	54	S114 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:24
S116	261	(204/196.06,228.6,229.8.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:14
S117	1063	(204/400,556.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:14
S118	35	S116 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near4 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:25
S119	109	S117 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near4 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:16
S120	0	S116 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near4 (molecular intra$1molecular) near4 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:16

S121	0	S117 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near4 (molecular intra$1molecular) near4 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:20
S122	0	S118 and (molecular intra$1molecular) near4 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:20
S123	2	S119 and (molecular intra$1molecular) near4 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:24
S124	731	(molecular intra$1molecular) near3 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:24
S125	646	S124 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 14:27
S126	308	S125 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:36
S127	4	S126 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:30

S128	13	S125 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 14:29
S129	4	S128 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 14:26
S130	40238	(check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 15:07
S131	35204	S130 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 14:27
S132	180	S131 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 14:49
S133	55	S132 and ((self adj assembl$5) self$1assembl$5 SAM mono$6film mono$1coat$3 mono$1layer mono$1sheet mono$1pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 14:44
S134	2	("6432723").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 14:44

S135	437	(422/82.02.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 14:55
S136	4	S135 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 14:58
S137	31	(heterogeneous mixex) adj2 mono$1layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 15:00
S138	25	S137 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 15:02
S139	0	S138 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential charge))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:54
S140	1951	(heterogeneous mixex (self adj assembl$5) self$1assembl$5 composite) adj2 (mono$1layer mono$6film mono$1coat$3 mono$1sheet mono$1pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:02
S141	1477	S140 and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 15:05

S142	61	S141 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential charge))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 15:06
S143	23	S142 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:59
S144	2641	(438/680-683.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:00
S145	2453	(438/656,676,677,925.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:02
S146	232	(438/451,452.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:02
S147	2	S144 and (heterogeneous mixex (self adj assembl$5) self$1assembl$5 composite) adj2 (mono$1layer mono$6film mono$1coat$3 mono$1sheet mono$1pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:57
S148	0	S145 and (heterogeneous mixex (self adj assembl$5) self$1assembl$5 composite) adj2 (mono$1layer mono$6film mono$1coat$3 mono$1sheet mono$1pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:12

S149	0	S146 and (heterogeneous mixex (self adj assembl$5) self$1assembl$5 composite) adj2 (mono$1layer mono$6film mono$1coat$3 mono$1sheet mono$1pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:12
S150	4440	(324/158.1.ccls.) and @ad<"20030402"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:51
S151	0	S150 and (heterogeneous mixex (self adj assembl$5) self$1assembl$5 composite) adj2 (mono$1layer mono$6film mono$1coat$3 mono$1sheet mono$1pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:51
S152	22	S150 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential charge))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:58
S153	3	S144 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential charge))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:58
S154	0	S145 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential charge))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:57
S155	0	S146 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 ((surface interfac$3) adj (voltage potential charge))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 16:57

S156	1	S152 and (check$3 detect$3 sens$3 measur$5 comput$3 calculat$3 $2valuat$3 examin$5 test$3 determin$3 recogniz$3 inspect$3 anal$5 monitor$3 diagnos$3 identif$7) near3 conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 17:01